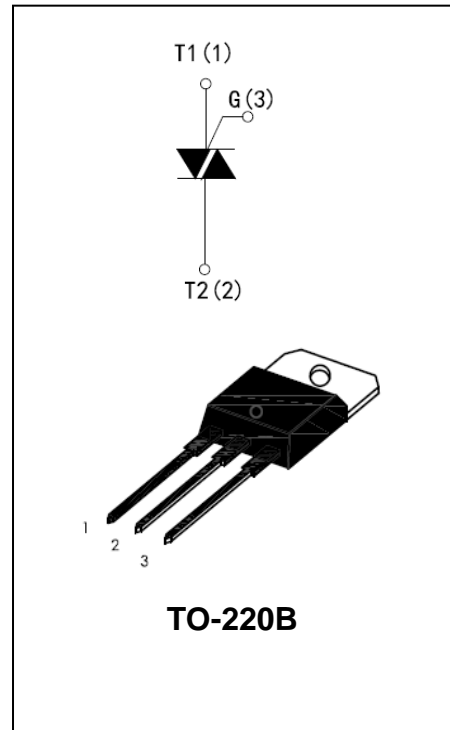




High current density due to double mesa technology; SIPOS and Glass Passivation. IPT0408-xx series are suitable for general purpose AC Switching. They can be used as an ON/OFF function In application such as static relays, heating regulation, Induction motor starting circuits... or for phase Control operation light dimmers, motor speed Controllers. IPT0408-xx series is 3 Quadrants triacs, This is specially recommended for use on inductive Loads..



### MAIN FEATURES

Symbol	Value	Unit
$I_T(RMS)$	4	A
$V_{DRM} / V_{RRM}$	800	V
$I_{GT}$	5 to 35	mA

### ABSOLUTE MAXIMUM RATINGS

Parameter	Symbol	Value	Unit
Storage Junction Temperature Range	$T_{stg}$	-40 to +150	°C
Operating Junction Temperature Range	$T_j$	-40 to +125	°C
Repetitive Peak Off-state Voltage Repetitive Peak Reverse Voltage	$V_{DRM}$ $V_{RRM}$	800 800	V
Non Repetitive Peak Off-state Voltage Non Repetitive Peak Reverse Voltage	$V_{DSM}$ $V_{RSM}$	900 900	V
RMS on-state current (Full sine wave)	$I_T(RMS)$	4	A
Non repetitive surge peak on-state Current (full cycle, $T_j = 25^\circ C$ )	$I_{TSM}$	38 35	A
$I^2t$ Value for fusing $t_p = 10ms$	$I^2t$	6	A <sup>2</sup> s
Critical Rate of rise of on-state current $I_G = 2xI_{GT}$ , $t_r \leq 100ns$ , $f = 120Hz$ , $T_j = 125^\circ C$	$di / dt$	50	A/us
Peak gate current	$I_{GM}$	4	A
Average gate power dissipation	$P_{G(AV)}$	1	W

## ELECTRICAL CHARACTERISTICS (T<sub>j</sub> = 25 °C unless otherwise specified)

Symbol	Test Condition	Quadrant		IPT0408-xxB			Unit
				05	10	35	
I <sub>GT</sub>	V <sub>D</sub> = 12V R <sub>L</sub> = 33Ω	I – II – III	MAX	5	10	35	mA
V <sub>GT</sub>		I – II – III	MAX	1.3			V
V <sub>GD</sub>	V <sub>D</sub> =V <sub>DRM</sub> , R <sub>L</sub> =3.3KΩ, T <sub>j</sub> = 125 °C	I – II – III	MIN	0.2			V
I <sub>L</sub>	I <sub>G</sub> = 1.2 I <sub>GT</sub>	I – III	MAX	10	25	50	mA
		II		15	30	60	
I <sub>H</sub>	I <sub>T</sub> = 500mA		MAX	10	15	35	mA
dV/dt	V <sub>D</sub> = 67% V <sub>DRM</sub> gate open T <sub>j</sub> = 125 °C		MIN	20	40	400	V/us
(di/dt) <sub>c</sub>	(dV/dt) c=0.1V/us T <sub>j</sub> = 125 °C		MIN	1.8	2.7	-	A/ms
	(dV/dt) c=10V/us T <sub>j</sub> = 125 °C			0.9	2.0	-	
	Without snubber T <sub>j</sub> = 125 °C			-	-	2.5	

## STATIC CHARACTERISTICS

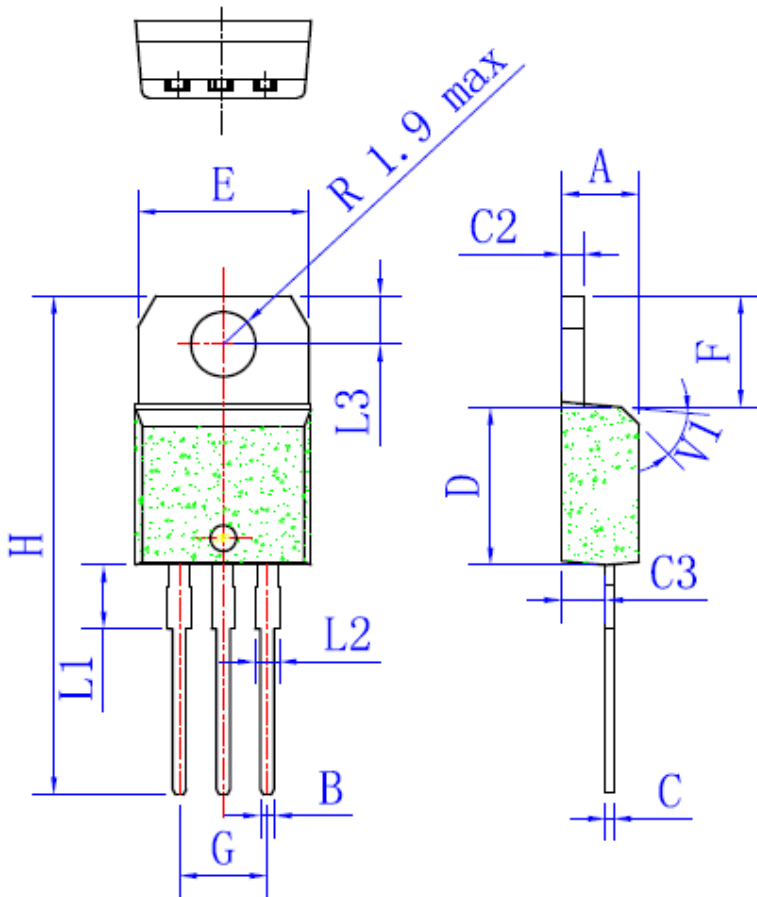
Symbol	Test Conditions		Value (MAX)	Unit
V <sub>TM</sub>	I <sub>TM</sub> = 5.5A, t <sub>p</sub> = 380uS	T <sub>j</sub> = 25 °C	1.6	V
I <sub>DRM</sub>	V <sub>D</sub> = V <sub>DRM</sub>	T <sub>j</sub> = 25 °C	5	uA
I <sub>RRM</sub>	V <sub>R</sub> = V <sub>RRM</sub>	T <sub>j</sub> = 125 °C	1	mA

## THERMAL RESISTANCES

Symbol	Parameter	Value	Unit
R <sub>th(j-c)</sub>	Junction to case (AC)	2.6	°C/W

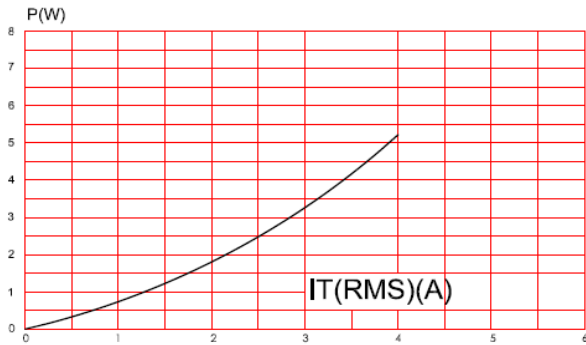
PACKAGE MECHANICAL DATA

TO-220B

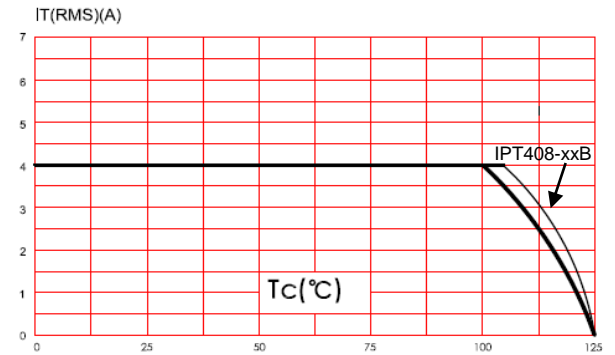


	Millimeters		
	Min	Typ	Max
A	4.4		4.6
B	0.61		0.88
C	0.46		0.70
C2	1.23		1.32
C3	2.4		2.72
D	8.6		9.7
E	9.8		10.4
F	6.2		6.6
G	4.8		5.4
H	28		29.8
L1		3.75	
L2	1.14		1.7
L3	2.65		2.95
V		40°	

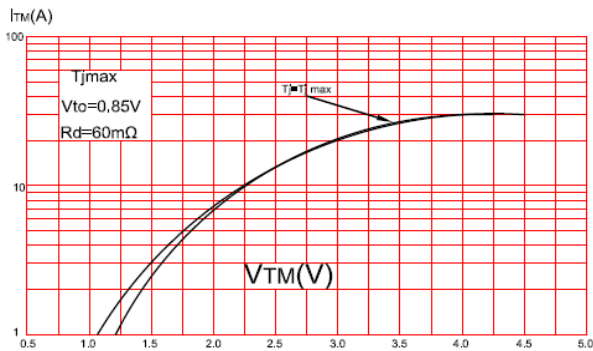
**FIG.1:** Maximum power dissipation versus RMS on-state current(full cycle)



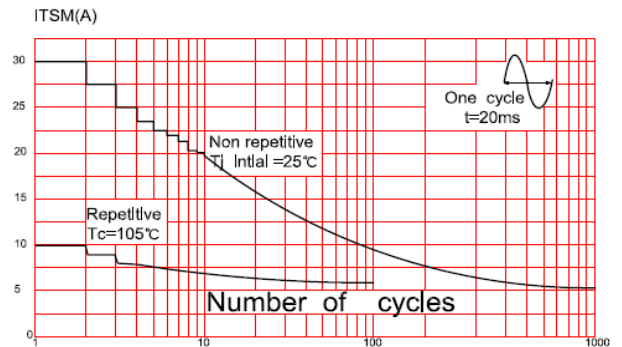
**FIG.2:** RMS on-state current versus case temperature(full cycle)



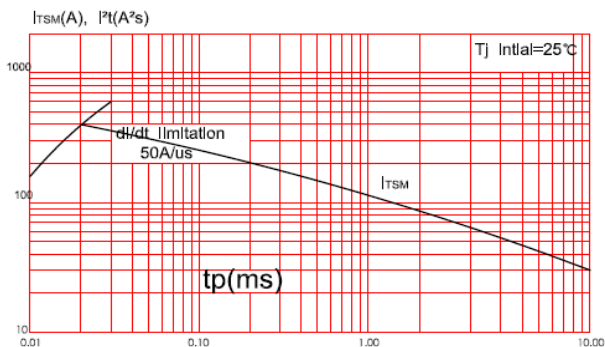
**FIG.3:** On-state characteristics (maximum values)



**FIG.4:** Surge peak on-state current versus number of cycles



**FIG.5:** Non-repetitive surge peak on-state current for a sinusoidal pulse with width  $t_p < 10\text{ms}$ .



**FIG.6:** Relative variations of gate trigger current, holding current and latching current versus junction temperature(typical values)

